

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A plasma generating electrode comprising at least two opposing plate-shaped unit electrodes, each having a rectangular surface and four end faces, and a holding member which holds ~~at least one (fixed end)~~ a fixed end of a first pair of parallel ~~ends (pair of ends)~~ ends of the unit electrode ~~corresponding to the four end faces~~ in a state in which the unit electrodes are separated at a specific interval, and is capable of generating plasma upon application of voltage between the unit electrodes,

at least one of the opposing unit electrodes being a conductive-film-containing electrode including a ceramic body as a dielectric and a conductive film disposed inside the ceramic body, and

a distance “a” (~~mm~~) from an edge of the conductive film to an edge of the ceramic body on ~~the a other second~~ a second pair of parallel ~~ends (other pair of ends)~~ ends of the conductive-film-containing electrode adjacent to the first pair of parallel ends ~~end faces~~ and a thickness “c” (~~mm~~) of the ceramic body satisfying a relationship “ $(c/2) \leq a \leq 5c$ ”.

2. (Currently Amended) The plasma generating electrode according to claim 1, wherein a distance “b” (~~mm~~) from the edge of the conductive film to the edge of the ceramic body on the fixed end of the conductive-film-containing electrode and the thickness “c” (~~mm~~) of the ceramic body satisfy a relationship “ $2c \leq b \leq 10c$ ”.

3. (Currently Amended) The plasma generating electrode according to claim 1, wherein, when the first pair of ~~ends~~ parallel end faces of the conductive-film-containing electrode has ~~an end (free end)~~ a free end opposite to other than the fixed end, a distance “d” (~~mm~~) from the edge of the conductive film to the edge of the ceramic body on the free end and the thickness “c” (~~mm~~) of the ceramic body satisfy a relationship “ $(c/2) \leq d \leq 5c$ ”.

4. (Previously Presented) The plasma generating electrode according to claim 1, wherein the conductive film has a thickness of 5 to 30 μm .

5. (Previously Presented) The plasma generating electrode according to claim 1, wherein the ceramic body includes at least one ceramic selected from the group consisting of alumina, mullite, ceramic glass, zirconia, cordierite, silicon nitride, aluminum nitride, and glass.

6. (Previously Presented) The plasma generating electrode according to claim 1, wherein the conductive film includes at least one metal selected from the group consisting of tungsten, molybdenum, manganese, chromium, titanium, zirconium, nickel, iron, silver, copper, platinum, and palladium.

7. (Currently Amended) A plasma reactor ~~comprising~~ comprising:
the plasma generating electrode according to ~~claim 1~~, claim 1; and
a casing having a gas passage ~~passage~~, ~~(gas passage)~~ ~~for a gas containing a~~
~~specific component formed therein~~, wherein, when ~~the~~ a gas is introduced into the gas
passage of the casing, ~~the~~ a specific component contained in the gas can be reacted using
plasma generated by the plasma generating electrode.

8. (Currently Amended) The plasma reactor according to claim 7, further
comprising a pulsed power supply for applying voltage to the plasma generating electrode.

9. (Original) The plasma reactor according to claim 8, wherein the pulsed power
supply includes at least one SI thyristor.

10. (New) The plasma generating electrode according to claim 1, wherein the
ceramic body is a dense ceramic and the ceramic body and the conductive film are integrated.